

**CMKT2222A**  
**ULTRAmi™**  
**SURFACE MOUNT**  
**DUAL NPN SMALL SIGNAL**  
**SWITCHING TRANSISTORS**

**ULTRAmi™**  
  
**SOT-363 CASE**

**Central™**  
**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMKT2222A type is a dual NPN small signal switching transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for small signal general purpose and switching applications. Marking Code is K22.

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

	SYMBOL		UNITS
Collector-Base Voltage	$V_{CBO}$	75	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	$I_C$	600	mA
Power Dissipation	$P_D$	350	mW
Operating and Storage			
Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\Theta_{JA}$	357	$^\circ\text{C}/\text{W}$

**ELECTRICAL CHARACTERISTICS PER TRANSISTOR:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CBO}$	$V_{CB}=60\text{V}$		10	nA
$I_{CBO}$	$V_{CB}=60\text{V}, T_A=125^\circ\text{C}$		10	$\mu\text{A}$
$I_{CEV}$	$V_{CE}=60\text{V}, V_{EB}=3.0\text{V}$		10	nA
$I_{EBO}$	$V_{EB}=3.0\text{V}$		10	nA
$BV_{CBO}$	$I_C=10\mu\text{A}$	75		V
$BV_{CEO}$	$I_C=10\text{mA}$	40		V
$BV_{EBO}$	$I_E=10\mu\text{A}$	6.0		V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.3	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		1.0	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	0.6	1.2	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		2.0	V
$h_{FE}$	$V_{CE}=10\text{V}, I_C=0.1\text{mA}$	35		
$h_{FE}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	50		
$h_{FE}$	$V_{CE}=10\text{V}, I_C=10\text{mA}$	75		
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=150\text{mA}$	50		
$h_{FE}$	$V_{CE}=10\text{V}, I_C=150\text{mA}$	100	300	
$h_{FE}$	$V_{CE}=10\text{V}, I_C=500\text{mA}$	40		

R0 ( 28-September 2001)

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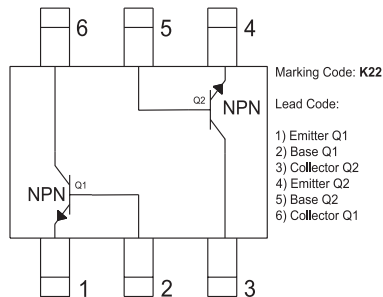
**ELECTRICAL CHARACTERISTICS PER TRANSISTOR CONTINUED:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$f_T$	$V_{CE}=20\text{V}, I_C=20\text{mA}, f=100\text{MHz}$	300		MHz
$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		8.0	pF
$C_{ib}$	$V_{EB}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$		25	pF
$h_{ie}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	2.0	8.0	$k\Omega$
$h_{ie}$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	0.25	1.25	$k\Omega$
$h_{re}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$		8.0	$\times 10^{-4}$
$h_{re}$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$		4.0	$\times 10^{-4}$
$h_{fe}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	50	300	
$h_{fe}$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	75	375	
$h_{oe}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	5.0	35	$\mu\text{hos}$
$h_{oe}$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	25	200	$\mu\text{hos}$
$rb'C_C$	$V_{CB}=10\text{V}, I_E=20\text{mA}, f=31.8\text{MHz}$		150	ps
NF	$V_{CE}=10\text{V}, I_C=100\text{mA}, R_S=1.0k\Omega, f=1.0\text{kHz}$		4.0	dB
$t_d$	$V_{CC}=30\text{V}, V_{BE}=0.5, I_C=150\text{mA}, I_{B1}=15\text{mA}$		10	ns
$t_r$	$V_{CC}=30\text{V}, V_{BE}=0.5, I_C=150\text{mA}, I_{B1}=15\text{mA}$		25	ns
$t_s$	$V_{CC}=30\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$		225	ns
$t_f$	$V_{CC}=30\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$		60	ns

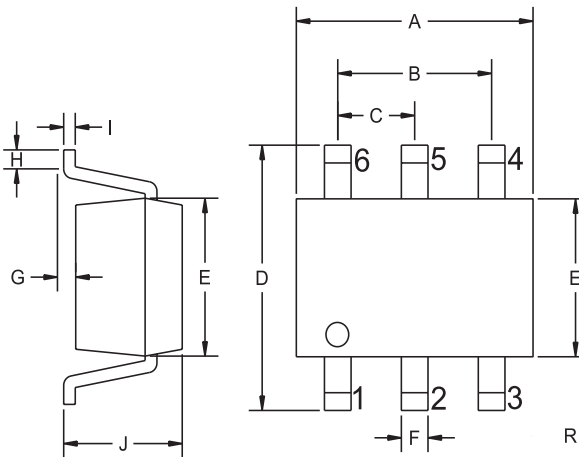
**SOT-363 CASE - MECHANICAL OUTLINE**

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
A	0.073	0.085	1.85	2.15
B	0.051		1.30	
C	0.026		0.65	
D	0.075	0.091	1.90	2.30
E	0.043	0.055	1.10	1.40
F	0.006	0.012	0.15	0.30
G	0.000	0.004	0.00	0.10
H	0.010	-	0.25	-
I	0.004	0.010	0.10	0.25
J	0.031	0.039	0.80	1.00

SOT-363 (REV: R1)



**MARKING CODE: K22**



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